

PolarHV™ Power MOSFET

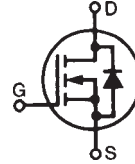
IXTC 26N50P

$$V_{DSS} = 500 \text{ V}$$

$$I_{D25} = 13 \text{ A}$$

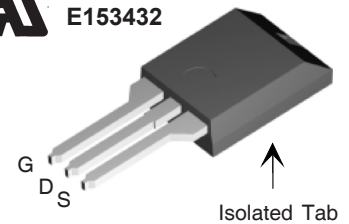
$$R_{DS(on)} = 260 \text{ m}\Omega$$

Electrically Isolated Tab,
N-Channel Enhancement Mode,
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	13	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	78	A
I_{AR}	$T_C = 25^\circ\text{C}$	26	A
E_{AR}	$T_C = 25^\circ\text{C}$	40	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, $t = 1$, leads-to-tab	2500	V~
F_C	Mounting Force	11..65/2.5..15	N/lb
Weight		2	g

ISOPLUS220™ (IXTC)
E153432



G = Gate D = Drain
S = Source

Features

- Silicon chip on Direct-Copper-Bond substrate
 - High power dissipation
 - Isolated mounting surface
 - 2500V electrical isolation
- Low drain to tab capacitance (<30pF)

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

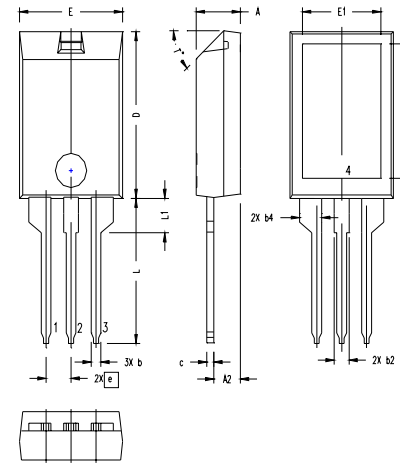
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			25 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = I_T$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			260 $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = I _T , pulse test	20	28	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		3600	pF
C_{oss}			380	pF
C_{rss}			48	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = I _T R _G = 4 Ω (External)		20	ns
t_r			25	ns
t_{d(off)}			58	ns
t_f			20	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = I _T		96	nC
Q_{gs}			20	nC
Q_{gd}			45	nC
R_{thJC}				1.25 K/W
R_{thCK}		0.21		K/W

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		Min.	typ.	Max.
I_S	V _{GS} = 0 V			26 A
I_{SM}	Repetitive			78 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = 25 A -di/dt = 100 A/μs		400	ns
Q_{RM}		V _R = 100 V		5.0

Note: Test Current I_T = 13A

ISOPLUS220 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T*			42.5*	47.5*

NOTE:

- Bottom heatsink (Pin 4) is electrically isolated from Pin 1, 2, or 3.
- This drawing will meet dimensional requirement of JEDEC SS Product Outline 10-273 except D and D1 dimension.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

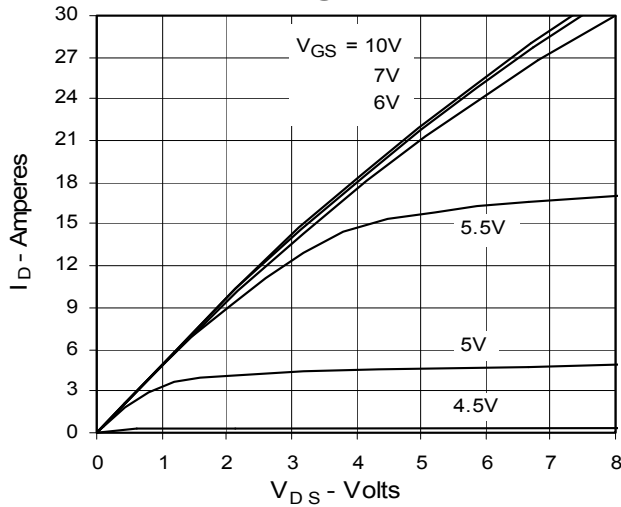
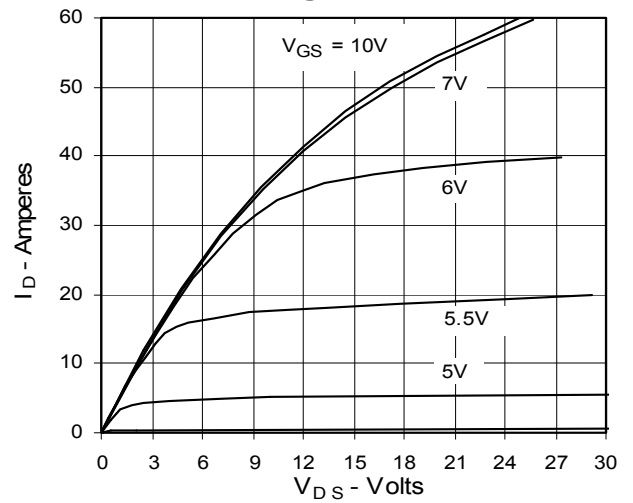
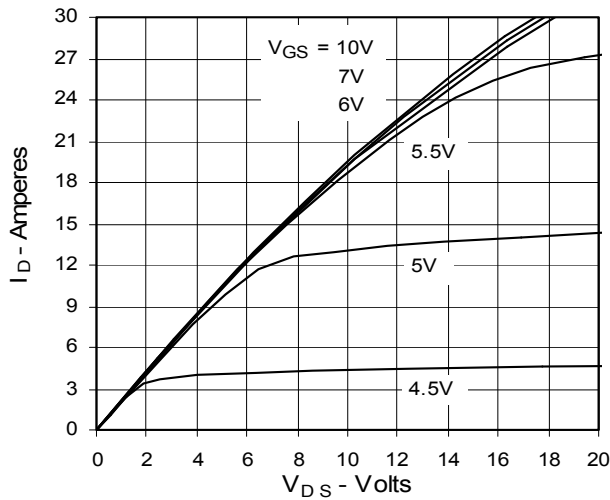
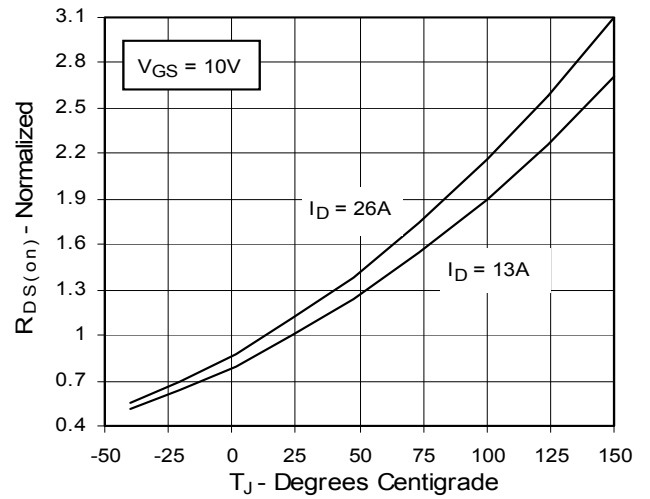
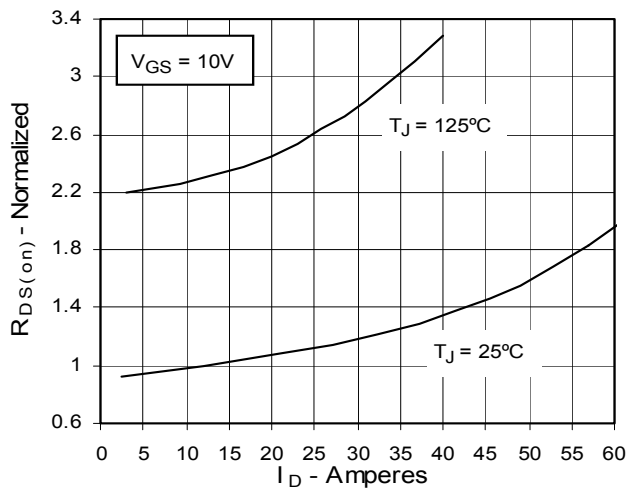
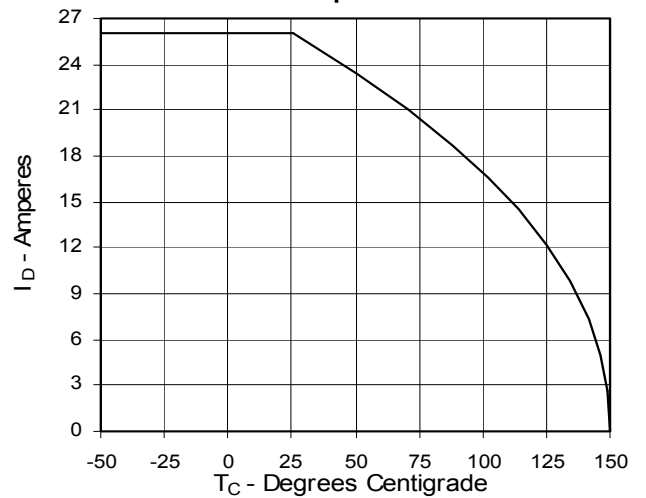
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**

**Fig. 6. Drain Current vs. Case
Temperature**


Fig. 7. Input Admittance

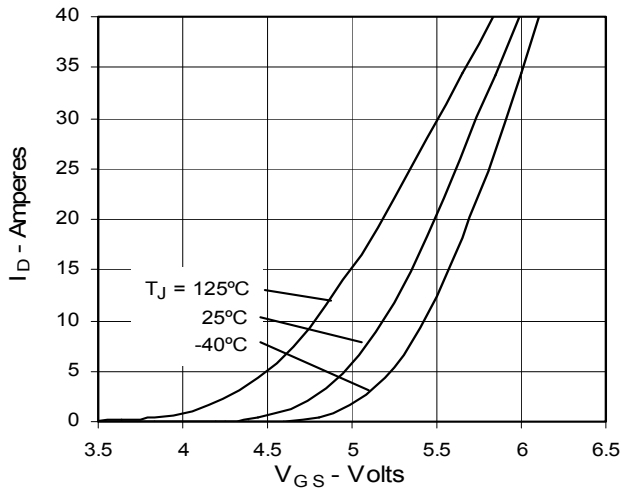


Fig. 8. Transconductance

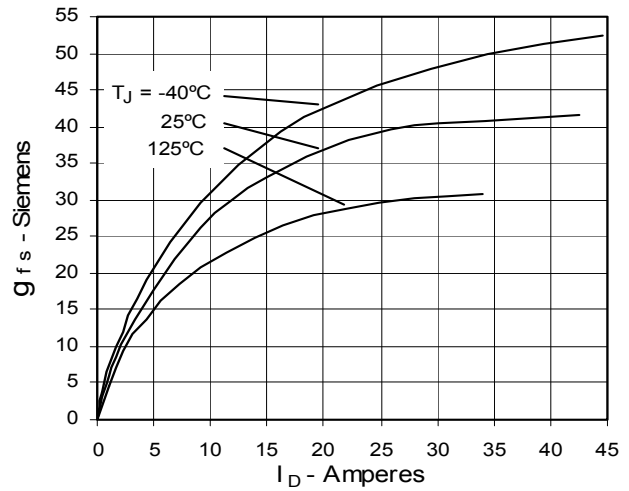


Fig. 9. Source Current vs. Source-To-Drain Voltage

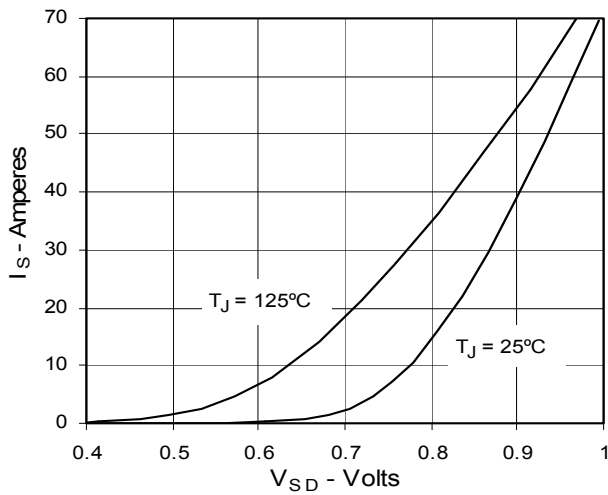


Fig. 10. Gate Charge

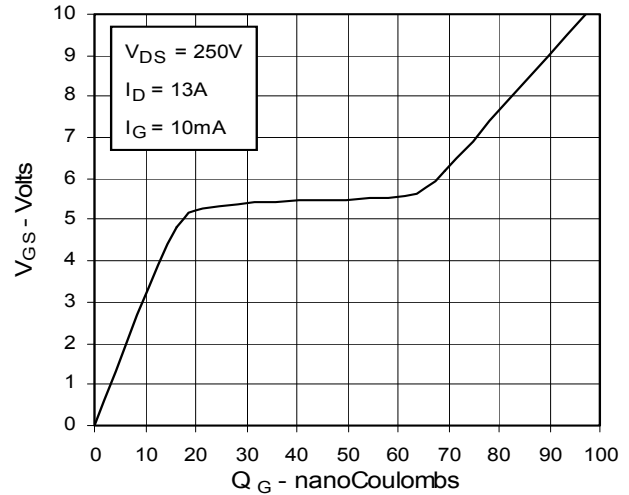


Fig. 11. Capacitance

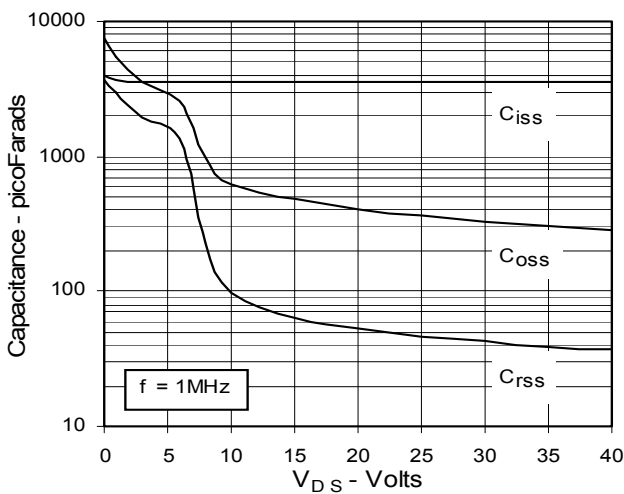


Fig. 12. Forward-Bias Safe Operating Area

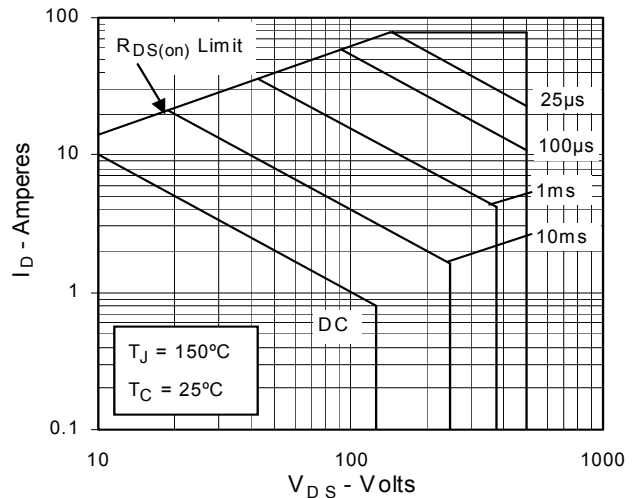


Fig. 13. Maximum Transient Thermal Resistance

